



## New Product

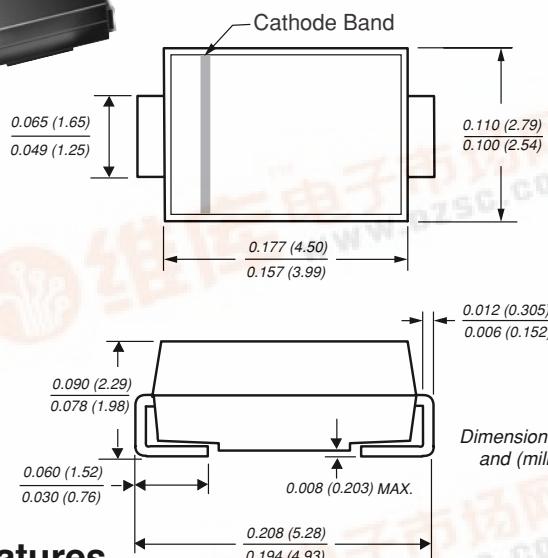
## SSA23L and SSA24

Vishay Semiconductors  
formerly General Semiconductor

## High-Current Density Surface Mount Schottky Rectifier



DO-214AC (SMA)

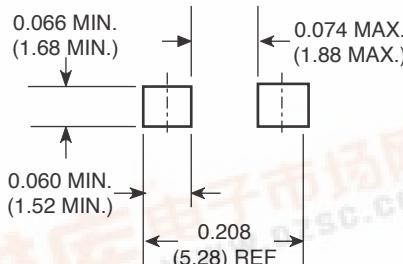


## Features

- Low power loss, high efficiency
- Low profile surface mount package
- Built-in strain relief
- For use in low voltage high frequency inverters, free wheeling, and polarity protection applications
- Guardring for overvoltage protection
- Plastic package has Underwriters Laboratory Flammability Classification 94V-0

Reverse Voltage 30 & 40 V  
Forward Current 2.0 A

## Mounting Pad Layout



## Mechanical Data

**Case:** JEDEC DO-214AC molded plastic body**Terminals:** Solder plated, solderable per MIL-STD750, Method 2026High temperature soldering guaranteed:  
250°C/10 seconds at terminals**Polarity:** Color band denotes cathode end**Weight:** 0.002 ounce, 0.064 gram

## Maximum Ratings and Thermal Characteristics (TA = 25°C unless otherwise noted)

| Parameter  | Symbol                               | SSA23L | SSA24        | Unit |
|--|--------------------------------------|--------|--------------|------|
| Device marking code  |                                      | 23L    | S24          | V    |
| Maximum repetitive peak reverse voltage  | V <sub>RRM</sub>                     | 30     | 40           | V    |
| Maximum RMS voltage  | V <sub>RMS</sub>                     | 21     | 28           | V    |
| Maximum DC blocking voltage  | V <sub>DC</sub>                      | 30     | 40           | V    |
| Maximum average forward rectified current at T <sub>L</sub> (See Fig. 1)                         | I <sub>F(AV)</sub>                   |        | 2.0          | A    |
| Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method) | I <sub>FSM</sub>                     |        | 60           | A    |
| Non-repetitive avalanche energy at TA = 25°C, IAS = 1.5A, L = 10mH                               | EAS                                  |        | 11.25        | mJ   |
| Typical thermal resistance <sup>(2)</sup>  | R <sub>θJA</sub><br>R <sub>θJL</sub> |        | 110<br>28    | °C/W |
| Voltage rate of change (rated VR)  | dv/dt                                |        | 10,000       | V/μs |
| Operating junction temperature range   | T <sub>J</sub>                       |        | -65 to + 150 | °C   |
| Storage temperature range  | T <sub>STG</sub>                     |        | -65 to + 150 | °C   |

## Electrical Characteristics (TA = 25°C unless otherwise noted)

| Parameter  | Symbol  | Typ.         | Max.         | Typ.         | Max.         | Unit |
|--|---|--------------|--------------|--------------|--------------|------|
| Maximum instantaneous forward voltage at 2.0A <sup>(1)</sup>           | V <sub>F</sub><br>T <sub>J</sub> =25°C<br>T <sub>J</sub> =125°C | 0.43<br>0.32 | 0.45<br>0.38 | 0.45<br>0.36 | 0.49<br>0.42 | V    |
| Maximum DC reverse current at rated DC blocking voltage <sup>(1)</sup> | I <sub>R</sub><br>T <sub>J</sub> =25°C<br>T <sub>J</sub> =125°C | —<br>15      | 0.5<br>25    | —<br>12      | 0.2<br>20    | mA   |

Notes: (1) Pulse test: 300μs pulse width, 1% duty cycle

(2) Aluminum substrate mounted



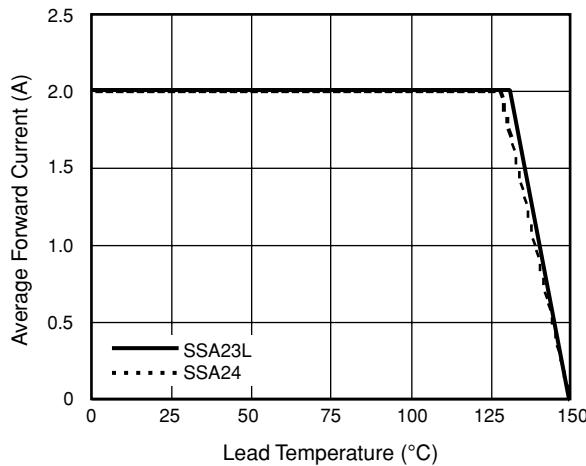
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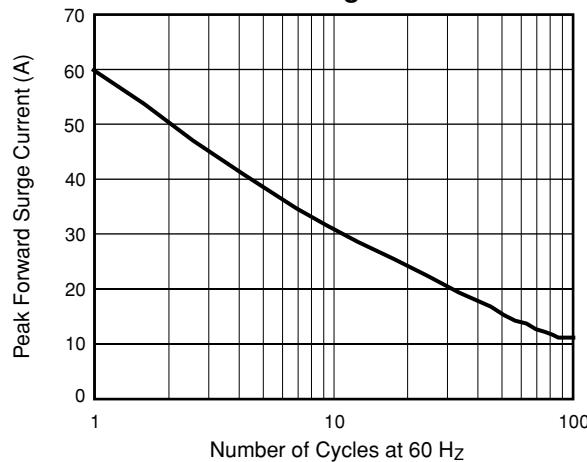


## Ratings and Characteristic Curves ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

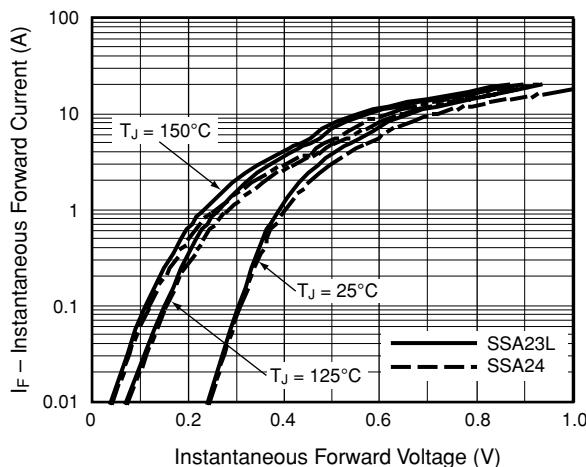
**Fig. 1 – Forward Current Derating Curve**



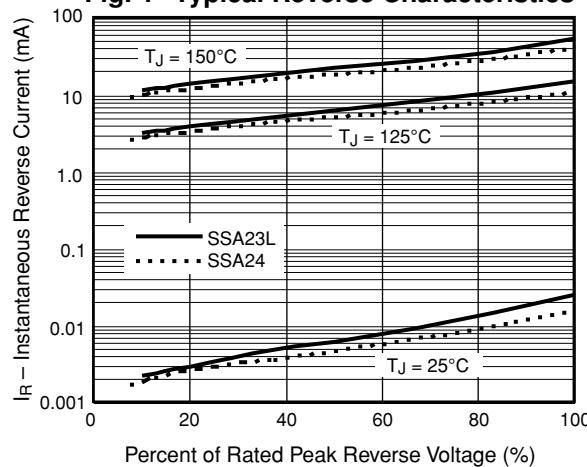
**Fig. 2 - Maximum Non-Repetitive Peak Forward Surge Current**



**Fig. 3 - Typical Instantaneous Forward Characteristics**



**Fig. 4 - Typical Reverse Characteristics**



**Fig. 5 - Typical Junction Capacitance**

